

Abstract Submitted  
for the OSF08 Meeting of  
The American Physical Society

**Capacitance-Voltage Properties of AlGaN Schottky Devices** A. DI MASCIO, M. AHOJJJA, S. ELHAMRI, R. BERNEY, Department of Physics, University of Dayton, OH — Electrical properties of Si doped AlGaN films, grown by radio-frequency plasma assisted molecular beam epitaxy, are investigated using variable frequency capacitance-voltage as a function of temperature. In particular, a comprehensive investigation of the properties of Ni/Au Schottky contacts as a function of temperature and frequency will be reported.

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Date submitted: 19 Sep 2008

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